

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

CHANG-YOUNG JEONG, ET AL.

Application No.:

Filed:

For: **METHOD FOR MANUFACTURING CMOS
IMAGE SENSOR HAVING MICROLENS
THEREIN WITH HIGH PHOTSENSITIVITY**

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

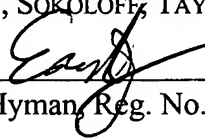
Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Date: _____

12/15/67

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

 Sheet **1** of **1**

Complete if Known

Application Number	
Filing Date	
First Named Inventor	Chang-Young JEONG
Art Unit	
Examiner Name	
Attorney Docket Number	51876P432

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-6,001,540	12-14-1999	Huang et al.	
		US-2002/0102498 A1	08-01-2002	Hsin	
		US-2002/0114526 A1	08-22-2002	Dennis	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP 04-025073	01-28-1992	TOPPAN PRINTING CO LTD		Abstract
		JP 06-326285	11-25-1994	SANYO ELECTRIC CO LTD		Abstract
		JP 06-326287	11-25-1994	SONY CORP		Abstract
		JP 08-001809	01-09-1996	CASIO COMPUT CO LTD		Abstract
		JP 05-029590	02-05-1993	TOSHIBA CORP		Abstract
		JP 2001-094085	04-06-2001	NEC CORP		Abstract
		JP 04-129268	04-03-1992	TOSHIBA CORP		Abstract

Examiner Signature		Date Considered	
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wtr) 08/11/2003.

Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Information Disclosure Statement

New U.S. Patent Application for
**METHOD FOR MANUFACTURING CMOS IMAGE SENSOR HAVING
MICROLENS THEREIN WITH HIGH PHOTSENSITIVITY**

Our Ref. No.: P03H8003/US/gy

Reference No.:

- (1) US Patent No. 6,001,540
- (2) US Publication No. 2002/0102498 A1
- (3) US Publication No. 2002/0114526 A1
- (4) JP Laid-Open No. 4-25073
- (5) JP Laid-Open No. 6-326285
- (6) JP Laid-Open No. 6-326287
- (7) JP Laid-Open No. 8-1809
- (8) JP Laid-Open No. 5-29590
- (9) JP Laid-Open No. 2001-94085
- (10) JP Laid-Open No. 4-129268